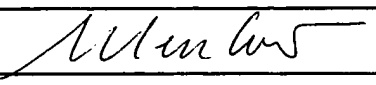


Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 108272.01		APPLICATION NO. Rule 53(b) Continuing Application of U.S. Application No. 09/748,207	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Yoshitaka SASAKI et al.			
				FILING DATE March 2, 2004			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
AC	1	6,083,410	07/2000	Ikegawa et al.	—	—	
AC	2	6,333,841	12/2001	Sasaki	—	—	
AC	3	6,459,551	10/2002	Hayakawa	—	—	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
AC	4	JP A 4-232250	08/1992	Japan	—	—	
AC	5	JP A 9-91618	04/1997	Japan	—	—	
AC	6	JP A 11-353616	12/1999	Japan	—	—	
AC	7	JP A 11-39614	12/1999	Japan	—	—	
AC	8	WO 99/41739	08/1999	WIPO	—	—	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
		Ericsson et al.; "Properties of Al ₂ O ₃ -films deposited on silicon by atomic layer epitaxy"; Microelectronic Engineering 36 (1997) 91-94					
EXAMINER					DATE CONSIDERED 1/30/06		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: March 2, 2004